Features

- Advanced Trench MOS Technology
- Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available

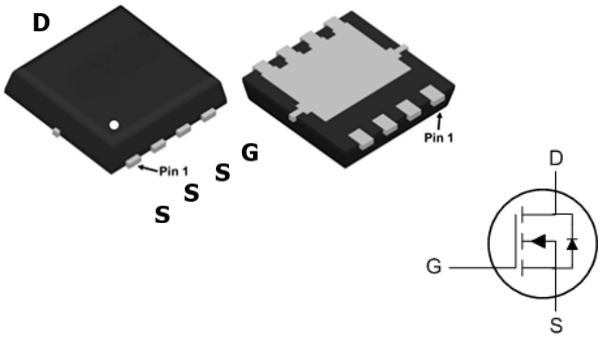
Product Summary

BVDSS	RDSON	ID
60V	12mΩ	33A

Application

- Motor Control.
- DC/DC Converter.
- Synchronous rectifier applications.

DFN 3x3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	33	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V[1]	20.7	A
I_{DM}	Pulsed Drain Current[2]	100	A
EAS	Single Pulse Avalanche Energy[3]	54	mJ
I_{AS}	Avalanche Current	33	A
P_D@T_C=25˚C	Total Power Dissipation[4]	20.8	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient[1]	---	60	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction-case[1]	---	6	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=12A	---	8	12	mΩ
		V_{GS}=4.5V , I_D=12A	---	13	18	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	2	2.3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
Rg	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.0	–––	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=30V , V_{GS}=10V , I_D=12A	---	15.8	---	nC
Q_g	Total Gate Charge (4.5V)			8.7		
Q_{gs}	Gate-Source Charge		---	3.1	---	
Q_{gd}	Gate-Drain Charge		---	4.4	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω, I_D=12A	---	5.8	---	ns
T_r	Rise Time		---	3.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	3.2	---	
C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , f=1MHz	---	760	---	pF
C_{oss}	Output Capacitance		---	272	---	
C_{rss}	Reverse Transfer Capacitance		---	26	---	
Diode Characteristics						
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	33	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1.The data tested by surface mounted on a 1 $inch^2$ FR-4 board with 2OZ copper.
2. Single pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=33A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_S , in real applications , should be limited by total power dissipation.

Typical Characteristics

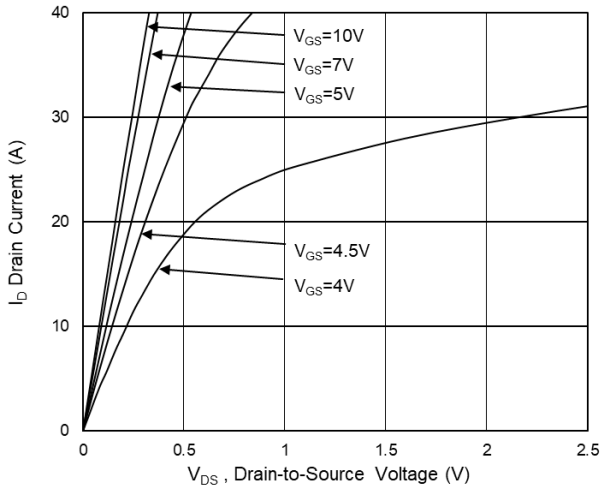


Fig.1 Typical Output Characteristics

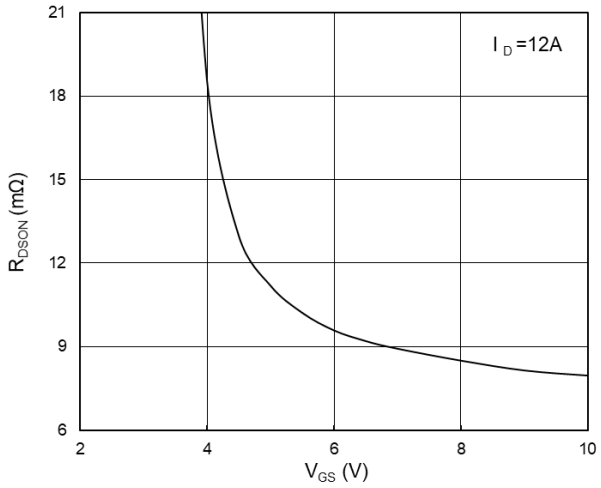


Fig.2 On-Resistance vs G-S Voltage

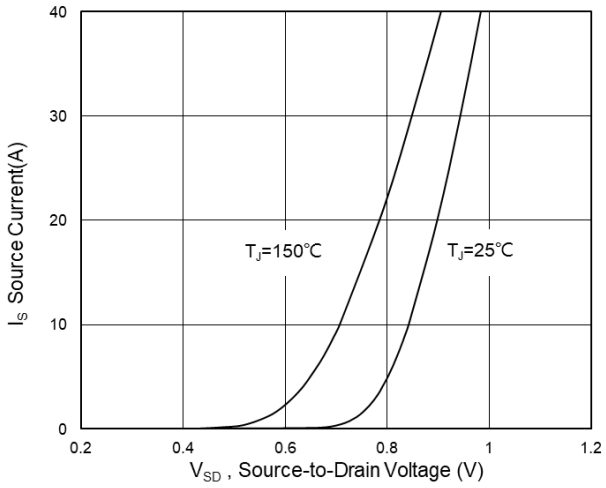


Fig.3 Source Drain Forward Characteristics

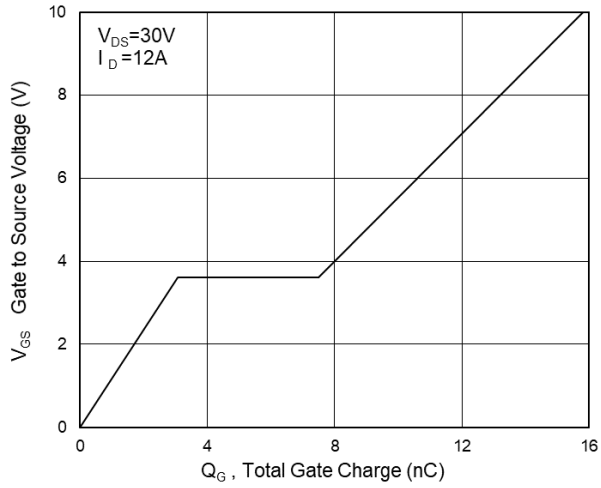


Fig.4 Gate-Charge Characteristics

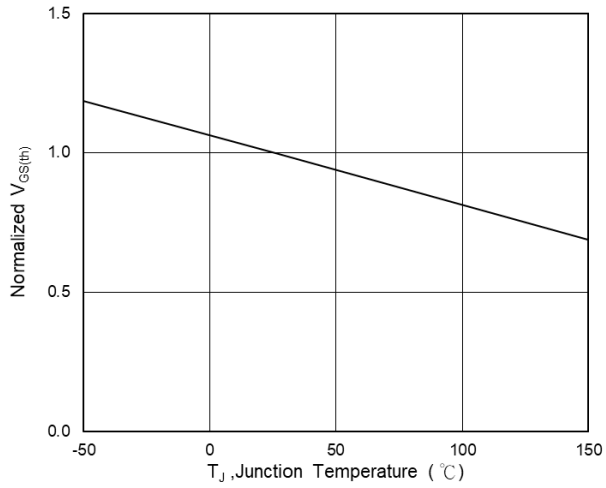


Fig.5 Normalized $V_{GS(th)}$ vs T_J

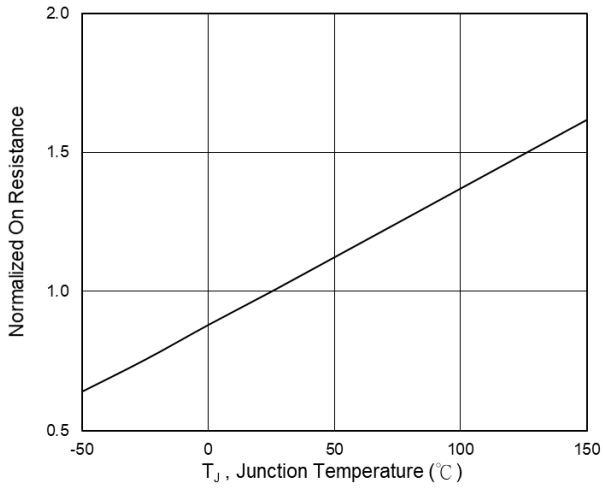


Fig.6 Normalized R_{DSON} vs T_J

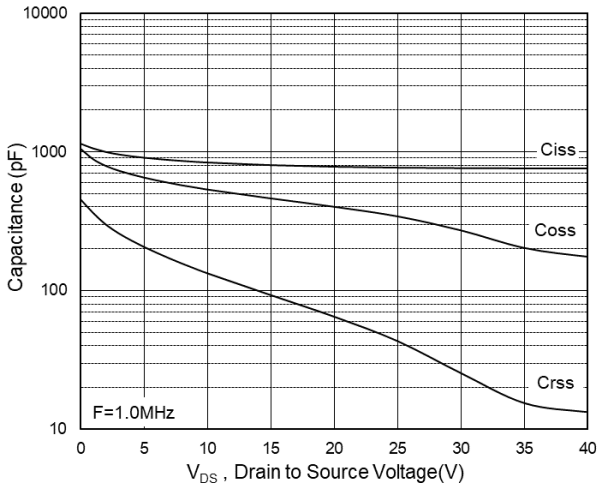


Fig.7 Capacitance

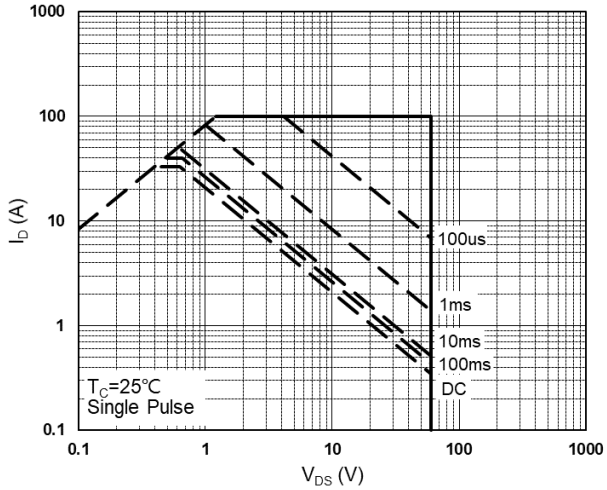


Fig.8 Safe Operating Area

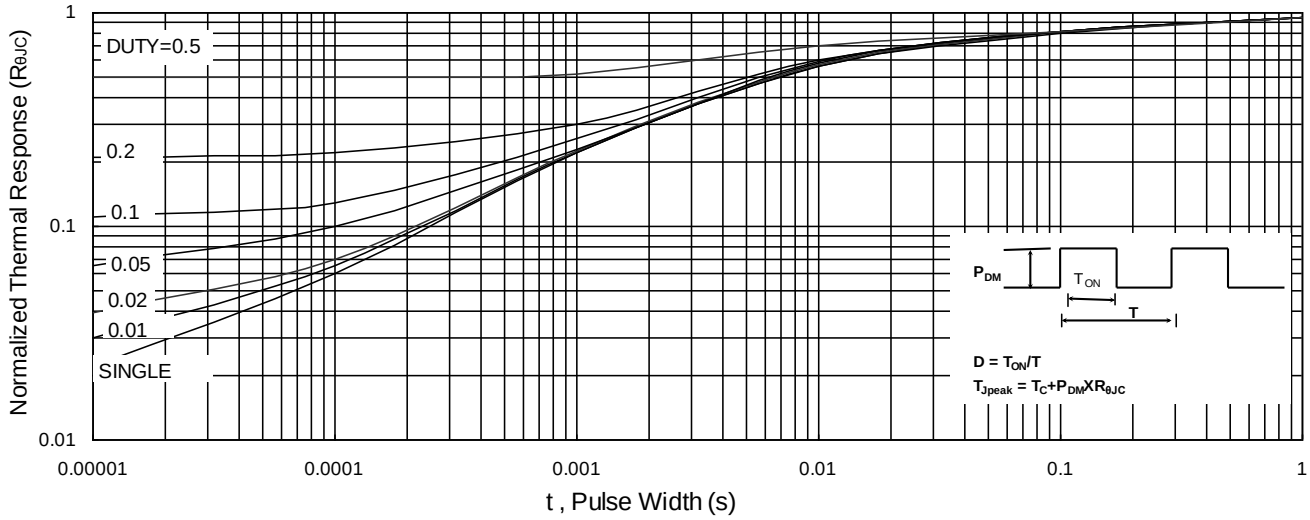


Fig.9 Normalized Maximum Transient Thermal Impedance

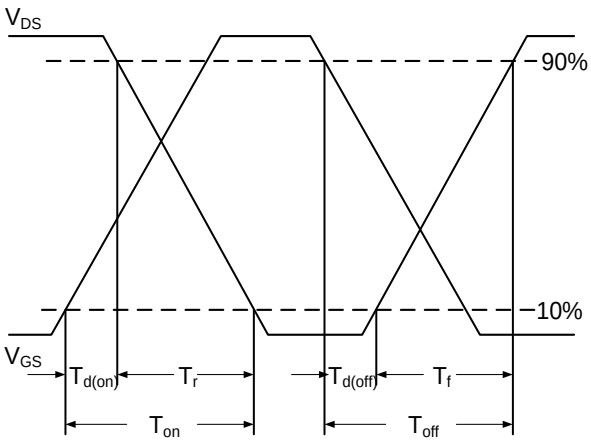


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

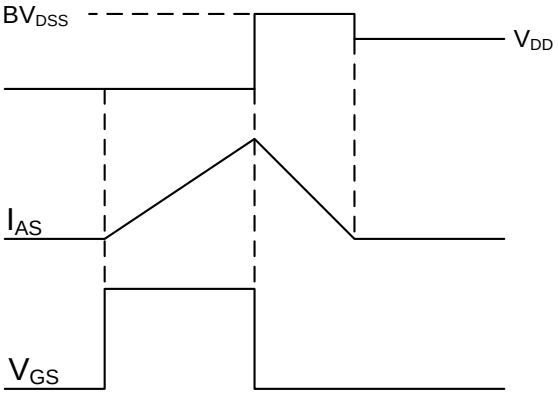
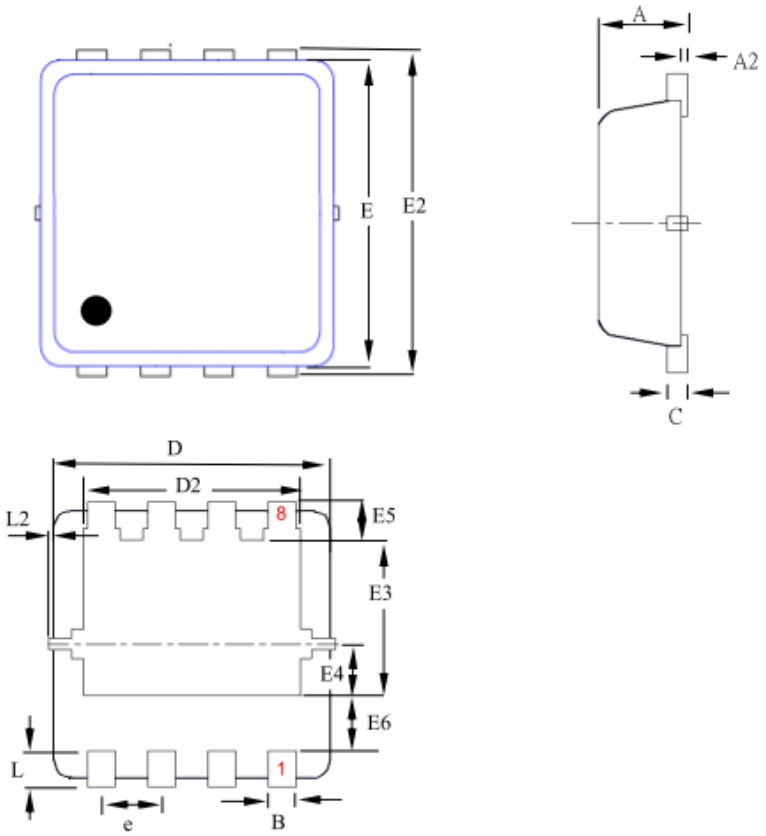


Fig.11 Unclamped Inductive Switching Waveform

DFN3*3 Package Outline Dimensions



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A2	0.00	--	0.05	0.000	--	0.002
B	0.24	0.30	0.35	0.009	0.012	0.014
C	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.20	0.114	0.118	0.126
D2	2.15	2.35	2.59	0.085	0.093	0.102
E	2.90	3.00	3.12	0.114	0.118	0.123
E2	3.05	3.20	3.45	0.120	0.126	0.136
E3	1.55	1.75	1.95	0.061	0.069	0.077
E4	0.48	0.58	0.68	0.019	0.023	0.027
E5	0.28	0.43	0.58	0.011	0.017	0.023
E6	0.43	0.63	0.87	0.017	0.025	0.034
L	0.30	0.40	0.50	0.012	0.016	0.020
L2	0.00	--	0.10	0.000	--	0.004
e	--	0.65	--	--	0.026	--

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